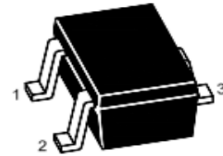
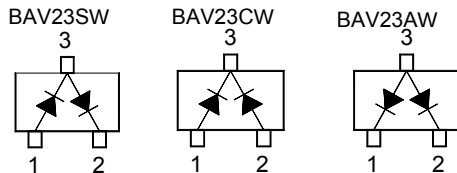




BAV23SW / CW / AW

Silicon Epitaxial Planar Diodes

High voltage switching diode



BAV23SW Marking Code: **V5**
BAV23CW Marking Code: **V9**
BAV23AW Marking Code: **V0**
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	250	V
Reverse Voltage	V_R	200	V
Forward Current	$I_{F(AV)}$	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1.7 3 9	A
Power Dissipation	P_{tot}	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100\ \text{mA}$ at $I_F = 200\ \text{mA}$	V_F	- -	1 1.25	V
Reverse Current at $V_R = 200\ \text{V}, T_j = 25^\circ\text{C}$ at $V_R = 200\ \text{V}, T_j = 150^\circ\text{C}$	I_R	- -	100 100	nA μA
Total Capacitance at $V_R = 0\ \text{V}, f = 1\ \text{MHz}$	C_{tot}	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\ \text{mA}, I_{tr} = 0.1 \times I_R, R_L = 100\ \Omega$	t_{rr}	-	50	ns



BAV23SW / CW / AW

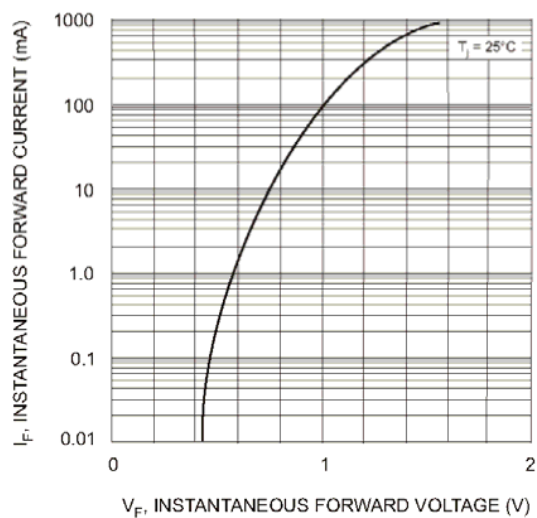


Fig. 1 Forward Characteristics

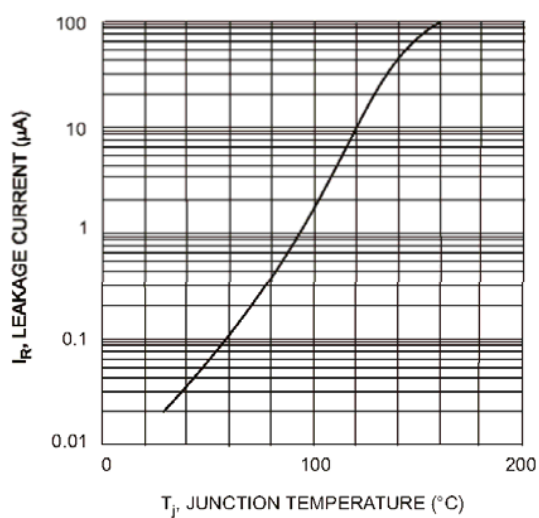


Fig. 2 Leakage Current vs Junction Temperature

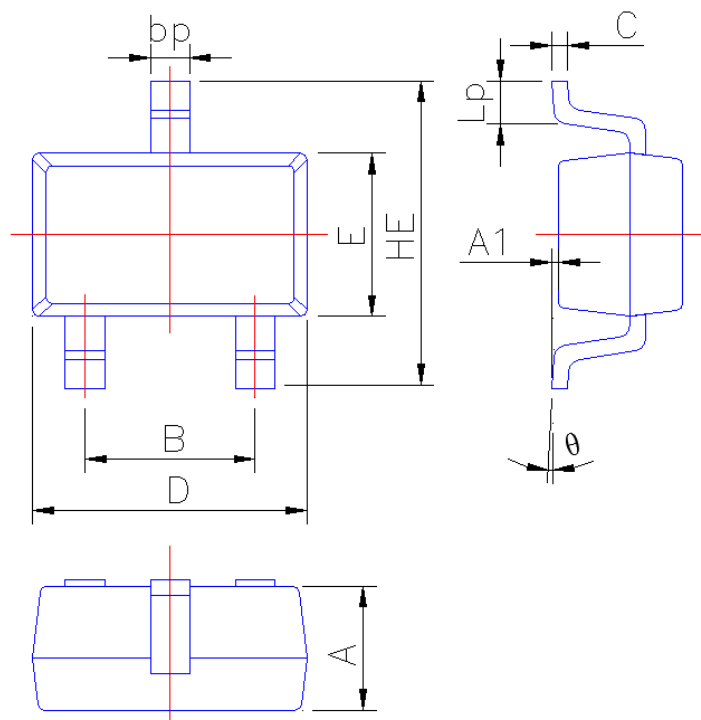


BAV23SW / CW / AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°